

ABSTRACT OF THE DISCLOSURE

A semiconductor device has: a semiconductor substrate having a principal surface; a fuse circuit formed above the principal surface, the fuse circuit having fuse elements each having a predetermined breaking point; a first trench isolation region formed in a surface layer of the semiconductor substrate under the fuse circuit; and a plurality of active region dummies formed through the first trench isolation region in an area excepting a predetermined area around the predetermined breaking point. Although a dummy structure is formed also in a fuse circuit, a breaking margin is prevented from being lowered and a substrate damage is avoided, while surface flatness and line width controllability are ensured.